

ELECTRICALLY ERASABLE PROGRAMMABLE READ ONLY MEMORY (EEPROM) CELL AND FORMING METHOD THEREOF

Abstract of Disclosure

An electrically erasable programmable read only memory (EEPROM) cell includes a first gate, a second gate and an erasing gate. The first gate and the second gate are disposed on a substrate, wherein the first gate includes a first floating gate and a first control gate stacked from bottom to top, and the second gate includes a second floating gate and a second control gate stacked from bottom to top. The erasing gate is sandwiched by the first gate and the second gate, wherein a side part of the first floating gate and a side part of the second floating gate right below the erasing gate both have multiple tips. The present invention also provides a method of forming said electrically erasable programmable read only memory (EEPROM) cell.

Figure 1